

Description

PECJ P-channel Enhancement Mode Power MOSFET

Features

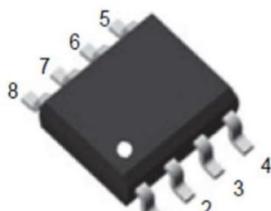
- $V_{DS} = -30V$, $I_D = -5.7A$
- $R_{DS(ON)} < 35m\Omega$ @ $V_{GS} = -10V$
- $R_{DS(ON)} < 56m\Omega$ @ $V_{GS} = -4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

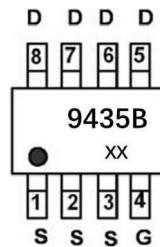
- PWM Applications
- Load Switch
- Power Management



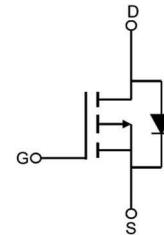
100% UIS TESTED!
100% ΔV_{ds} TESTED!



SOP-8 top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
9435B	PECJ9435B	TAPING	SOP-8	13inch	4000	48000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	-5.7	A
		$T_A = 100^\circ C$	-3.7	A
I_{DM}	Pulsed Drain Current ^{note1}		-22.8	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}		39.2	mJ
P_D	Power Dissipation	$T_A = 25^\circ C$	1.47	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		85	$^\circ C/W$
T_J , T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D = -250\mu\text{A}$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -30\text{V}$, $V_{GS}=0\text{V}$,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0\text{V}$, $V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D = -250\mu\text{A}$	-1.0	-1.5	-2.5	V
$R_{DS(\text{on})}$ note3	Static Drain-Source on-Resistance	$V_{GS} = -10\text{V}$, $I_D = -4\text{A}$	-	26.5	35	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}$, $I_D = -2\text{A}$	-	40	56	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -15\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$	-	757	-	pF
C_{oss}	Output Capacitance		-	122	-	pF
C_{rss}	Reverse Transfer Capacitance		-	88	-	pF
Q_g	Total Gate Charge	$V_{DS} = -15\text{V}$, $I_D = -3\text{A}$, $V_{GS} = -10\text{V}$	-	17.7	-	nC
Q_{gs}	Gate-Source Charge		-	3.3	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	2.3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = -15\text{V}$, $I_D = -1\text{A}$, $V_{GS} = -10\text{V}$, $R_{\text{GEN}} = 6\Omega$	-	4.6	-	ns
t_r	Turn-on Rise Time		-	14	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	34	-	ns
t_f	Turn-off Fall Time		-	18	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	-5.7	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	-22.8	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = -5.7\text{A}$	-	-0.8	-1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^\circ\text{C}$, $V_{DD} = -15\text{V}$, $V_G = -10\text{V}$, $R_G = 25\Omega$, $L = 0.1\text{mH}$, $I_{AS} = -28\text{A}$

3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

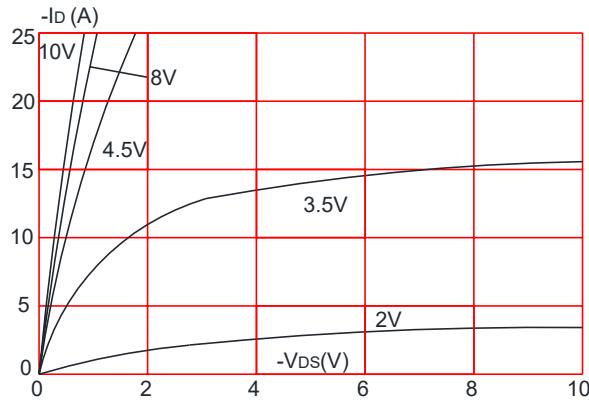


Figure 3: On-resistance vs. Drain Current

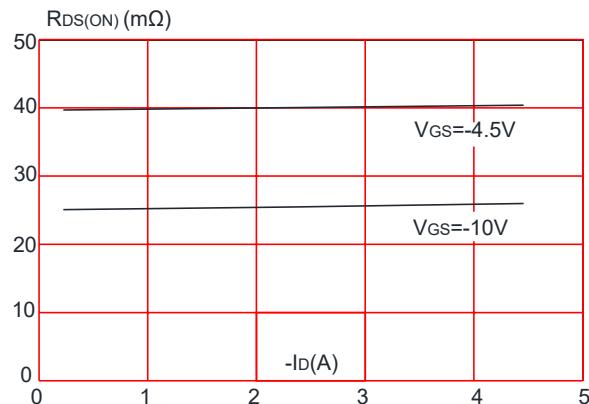


Figure 5: Gate Charge Characteristics

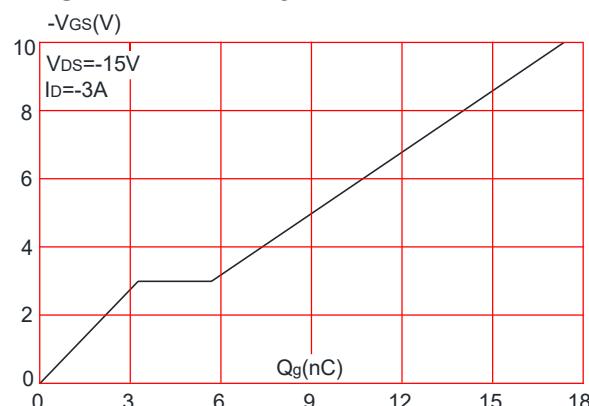


Figure 2: Typical Transfer Characteristics

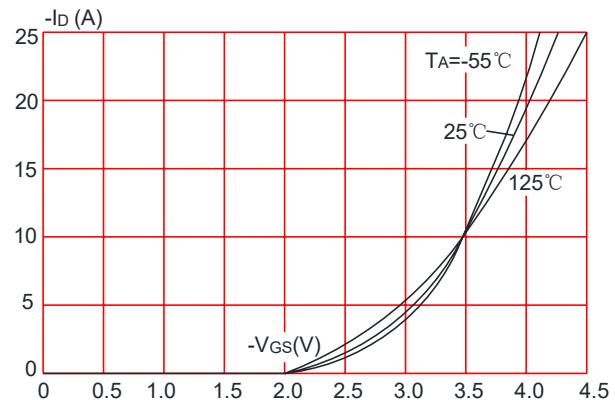


Figure 4: Body Diode Characteristics

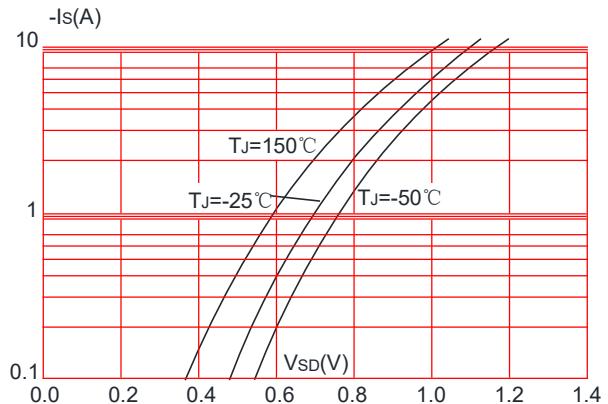


Figure 6: Capacitance Characteristics

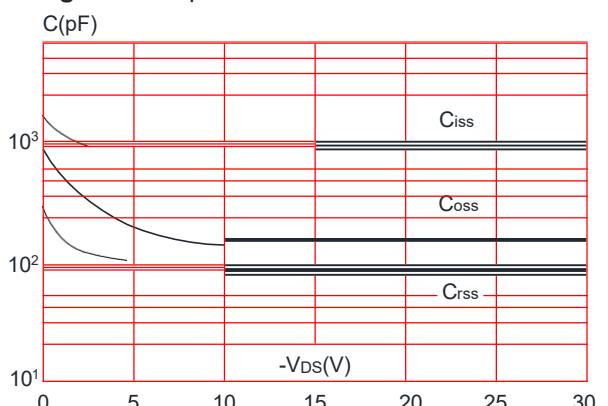


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

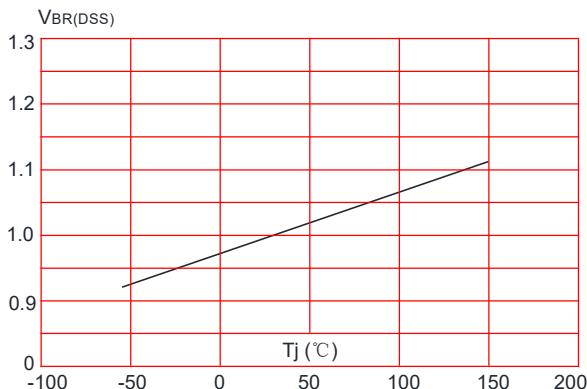


Figure 8: Normalized on Resistance vs. Junction Temperature

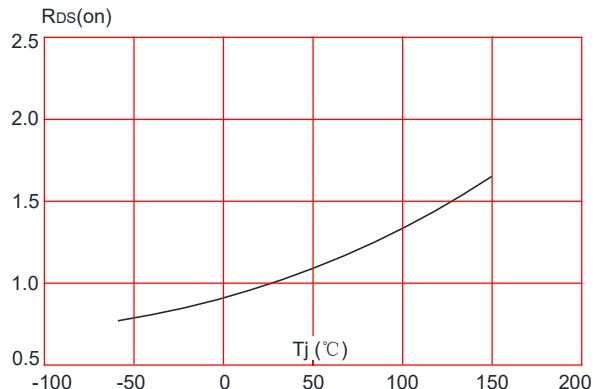


Figure 9: Maximum Safe Operating Area

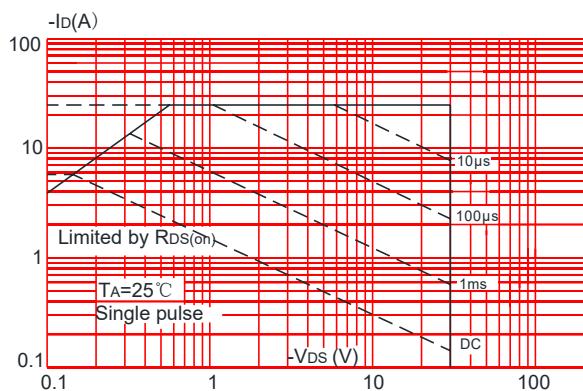


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

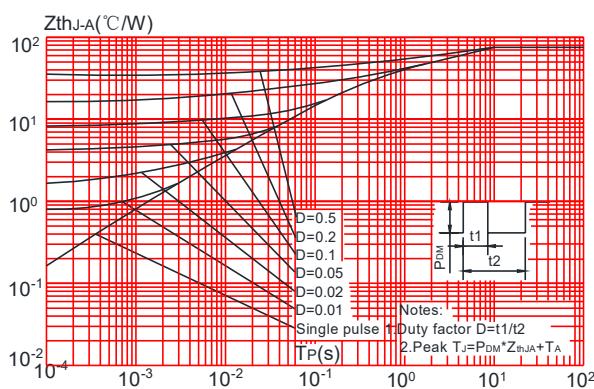
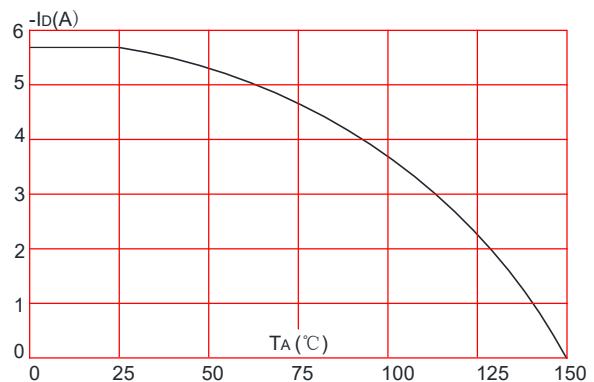
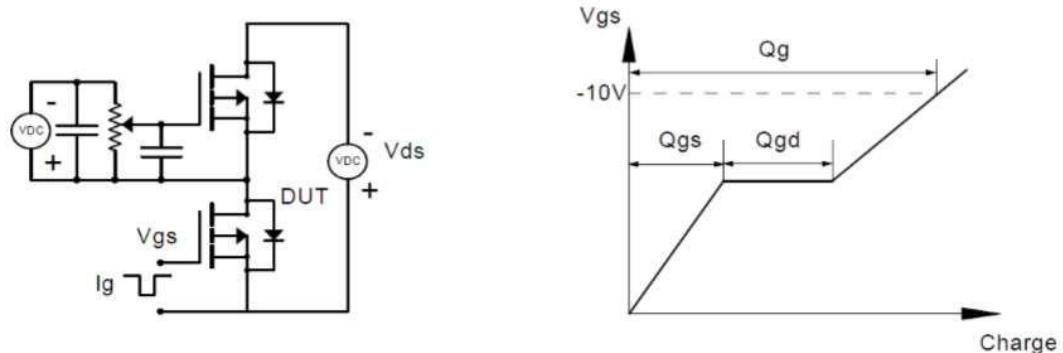


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

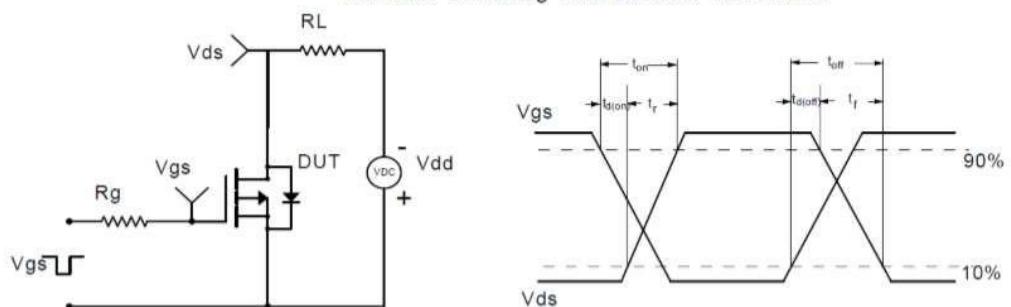


Test Circuit

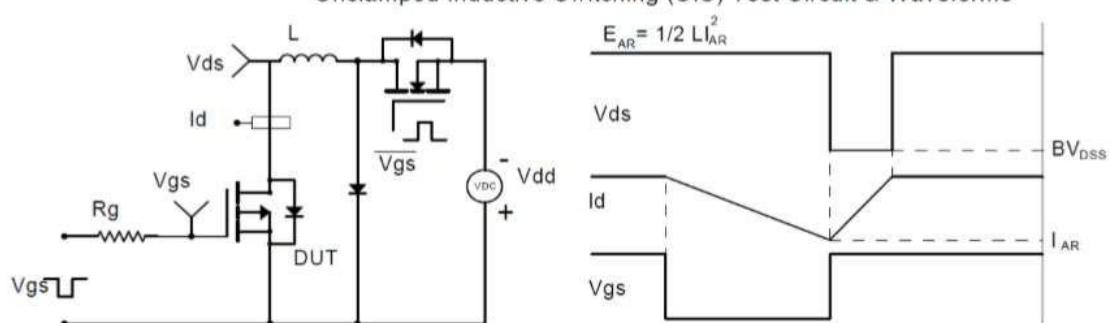
Gate Charge Test Circuit & Waveform



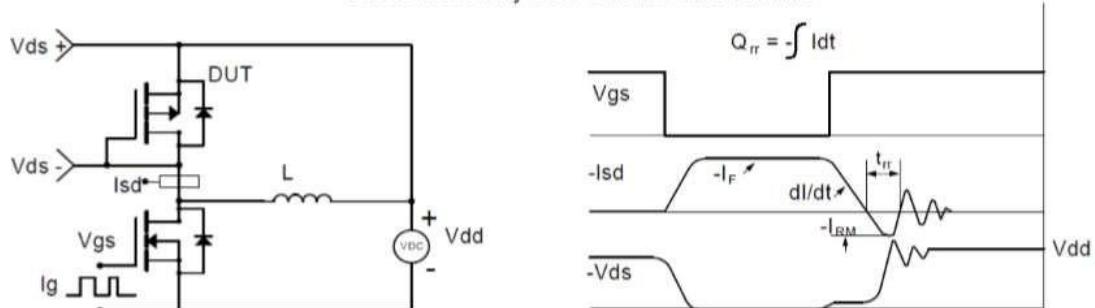
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Mechanical Data- SOP-8

